

QUERY CONTROL FORM		RTIS USE ONLY	
Application No.	09/852,999	Prepared by	NH
Examiner-GAU	Pham - 2814 ?	Date	3-2-4
		No. of queries	1
		Tracking Number	05896899
		Week Date	02/02/04
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JACKET			
a. Serial No.	f. Foreign Priority	k. Print Claim(s)	p. <u>PTO-1449</u>
b. Applicant(s)	g. Disclaimer	l. Print Fig.	q. PTOL-85b
c. Continuing Data	h. Microfiche Appendix	m. Searched Column	r. Abstract
d. PCT	i. Title	n. PTO-270/328	s. Sheets/Figs
e. Domestic Priority	j. Claims Allowed	o. PTO-892	t. Other

- a. Claim(s) Missing
- b. Improper Dependency
- c. Duplicate Numbers
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PTO-1449. Please either initial or line through citations. Copy provided for reference.

RESPONSE

Done. Tho sk

Thankyou

initials NH

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Based on Form PTO-1449
(3/90)ATTY. DOCKET NO.
452080-2010SERIAL NO.
09/331,528LIST OF REFERENCES CITED BY APPLICANT
(Use several sheets if necessary)APPLICANT
Hans Meiling et al.FILING DATE
August 5, 1999GROUP
281411033 U.S. PTO
09/852999
05/10/01

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLAS S	FILING DATE IF APPROPRIATE
LM	AA	4,634,605	01/6/1987	Wiesman			
	AB	4,485,128	11/24/84	Dala et al.			
	AC	4,465,706	8/14/84	Dala et al.			
	AD	5,397,737	3/14/84	Mahan et al.			
	AE	5,500,047	3/19/96	Park et al.			
	AF	5,776,819	7/7/98	Mahan et al.			
	AG	5,798,137	08/25/98	Lord et al.			
	AH	5,281,546	1/25/94	Possin et al.			
	AI	4,747,077	5/24/88	Hockley et al.			
gr	AJ	4,237,151	12/2/80	Strongin et al.			
	AK						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
gr	AL	0 687 753	12/20/95	Europe			
gr	AM	43 33 416	4/6/95	Germany			
	AN						
	AO						
	AP						

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

gr	AO	Meiling H. et al. "Stability of hot-wire deposited amorphous-silicon thin-film transistors". Applied Physics Letters. 19 August 1996. AIP. USA, vol. 69, no. 8. ISSN 0003-6951. pages 1062-1064. XP000626137
	AR	Kikuo Ono et al. "Inverse-Staggered Polycrystalline Silicon thin Film Transistors Fabricated By Excimer Laser Irradiation". Electronics 8 vol. 76, no. 12, December, 1993, pages 40-46. XP000468568
gr	AS	Doyle R. et al. "Production of high-quality amorphous silicon films by evaporative silane surface decomposition". Journal of Applied Physics. 15 Sept. 1988. USA, vol. 64, no. 6. ISSN 0021-8979. pages 3215-3223. XP000097188
	AT	Japanese Abstract of 01-162769, dated June 27, 1989; Araki Nakoto: FORMATION OF AMORPHOUS SILICON

EXAMINER

DATE CONSIDERED

March 16/2004

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.